AMD Xilinx - XCZU19EG-1FFVC1760I Datasheet

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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Quad ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™, ARM Mali™-400 MP2
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	500MHz, 600MHz, 1.2GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 1143K+ Logic Cells
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	1760-BBGA, FCBGA
Supplier Device Package	1760-FCBGA (42.5x42.5)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu19eg-1ffvc1760i

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Recommended Operating Conditions

Table 2: **Recommended Operating Conditions(1)(2)**

Symbol	Description	Min	Typ	Max	Units
Processor System					
$V_{CC\_PSINTFP}$(3)	PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS full-power domain supply voltage.	0.873	0.900	0.927	V
$V_{CC\_PSINTLP}$	PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS low-power domain supply voltage.	0.873	0.900	0.927	V
V_{CC_PSAUX}	PS auxiliary supply voltage.	1.710	1.800	1.890	V
$V_{CC\_PSINTFP\_DDR}$(3)	PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS DDR controller and PHY supply voltage.	0.873	0.900	0.927	V
V_{CC_PSADC}	PS SYSMON ADC supply voltage relative to GND_PSADC.	1.710	1.800	1.890	V
V_{CC_PSPLL}	PS PLL supply voltage.	1.164	1.200	1.236	V
$V_{PS\_MGTRAVCC}$	PS-GTR supply voltage.	0.825	0.850	0.875	V
$V_{PS\_MGTRAVTT}$	PS-GTR termination voltage.	1.746	1.800	1.854	V
V_{CCO_PSDDR}(4)	PS DDR I/O supply voltage.	1.06	–	1.575	V
$V_{CC\_PSDDR\_PLL}$	PS DDR PLL supply voltage.	1.710	1.800	1.890	V
V_{CCO_PSIO}(5)	PS I/O supply.	1.710	–	3.465	V
V_{PSIN}	PS I/O input voltage.	–0.200	–	$V_{CCO\_PSIO} + 0.200$	V
	PS DDR I/O input voltage.	–0.200	–	$V_{CCO\_PSDDR} + 0.200$	
V_{CC_PSBATT}(6)	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	1.200	–	1.500	V
Programmable Logic					
V_{CCINT}	PL internal supply voltage.	0.825	0.850	0.876	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PL internal supply voltage.	0.698	0.720	0.742	V
	For -3E devices: PL internal supply voltage.	0.873	0.900	0.927	V
V_{CCINT_IO}(7)	PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -3E devices: PL internal supply voltage for the I/O banks.	0.873	0.900	0.927	V
V_{CCBRAM}	Block RAM supply voltage.	0.825	0.850	0.876	V
	For -3E devices: block RAM supply voltage.	0.873	0.900	0.927	V
V_{CCAUX}	Auxiliary supply voltage.	1.746	1.800	1.854	V

Table 11: **Power Supply Ramp Time *(Cont'd)***

Symbol	Description	Min	Max	Units
T_{VCCO_PSDDR}	Ramp time from GND to 95% of V_{CCO_PSDDR}.	0.2	40	ms
$T_{VCC\_PSDDR\_PLL}$	Ramp time from GND to 95% of $V_{CC\_PSDDR\_PLL}$.	0.2	40	ms
T_{VCCO_PSIO}	Ramp time from GND to 95% of V_{CCO_PSIO}.	0.2	40	ms

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DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

PS I/O Levels

Table 12: **PS MIO and CONFIG DC Input and Output Levels**[1]

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
LVCMOS33	–0.300	0.800	2.000	V_{CCO_PSIO}	0.40	2.40	12	–12
LVCMOS25	–0.300	0.700	1.700	V_{CCO_PSIO} + 0.30	0.70	1.70	12	–12
LVCMOS18	–0.300	35% V_{CCO_PSIO}	65% V_{CCO_PSIO}	V_{CCO_PSIO} + 0.30	0.45	V_{CCO_PSIO} – 0.45	12	–12

Notes:

1. Tested according to relevant specifications.

Table 13: **PS DDR DC Input and Output Levels**[1]

DDR Standard	V_{IL}		V_{IH}		V_{OL}[2]	V_{OH}[2]	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
DDR4	0.000	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.8 x V_{CCO_PSDDR} – 0.150	0.8 x V_{CCO_PSDDR} + 0.150	10	–0.1
LPDDR4	0.000	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.3 x V_{CCO_PSDDR} – 0.150	0.3 x V_{CCO_PSDDR} + 0.150	0.1	–10
DDR3	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.5 x V_{CCO_PSDDR} – 0.175	0.5 x V_{CCO_PSDDR} + 0.175	8	–8
LPDDR3	0.000	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.5 x V_{CCO_PSDDR} – 0.150	0.5 x V_{CCO_PSDDR} + 0.150	8	–8
DDR3L	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO_PSDDR}	0.5 x V_{CCO_PSDDR} – 0.150	0.5 x V_{CCO_PSDDR} + 0.150	8	–8

Notes:

1. Tested according to relevant specifications.
2. DDR4 V_{OL}/V_{OH} specifications are only applicable for DQ/DQS pins.

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. Table 26 correlates the current status of the Zynq UltraScale+ MPSoC on a per speed grade basis. See Table 3 for operating voltages listed by speed grade.

Table 26: **Speed Grade Designations by Device**

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCZU2CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU2EG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU3CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU3EG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU4CG	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU4EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU4EV	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU5CG	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		

Table 72: **MIPI D-PHY Performance**

Description	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3(1)	-2(1)	-1	-2	-1	
MIPI D-PHY transmitter or receiver.	HP	1500	1500	1260	1260	1260	Mb/s

Notes:

1. In the SBVA484 package, the data rate is 1260 Mb/s.

Table 73: **LVDS Native-Mode 1000BASE-X Support(1)**

Description	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages				
		0.90V	0.85V		0.72V	
		-3	-2	-1	-2	-1
1000BASE-X	HP	Yes				

Notes:

1. 1000BASE-X support is based on the *IEEE Standard for CSMA/CD Access Method and Physical Layer Specifications* (IEEE Std 802.3-2008).

Table 74 provides the maximum data rates for applicable memory standards using the Zynq UltraScale+ MPSoC memory PHY. Refer to Memory Interfaces for the complete list of memory interface standards supported and detailed specifications. The final performance of the memory interface is determined through a complete design implemented in the Vivado Design Suite, following guidelines in the *UltraScale Architecture PCB Design Guide* (UG583), electrical analysis, and characterization of the system.

Table 74: **Maximum Physical Interface (PHY) Rate for Memory Interfaces**

Memory Standard	Package(1)	DRAM Type	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
DDR4	All FFV packages and FBVB900	Single rank component	2666	2666	2400	2400	2133	Mb/s
		1 rank DIMM(2)(3)(4)	2400	2400	2133	2133	1866	Mb/s
		2 rank DIMM(2)(5)	2133	2133	1866	1866	1600	Mb/s
		4 rank DIMM(2)(6)	1600	1600	1333	1333	N/A	Mb/s
	SFVC784	Single rank component	2400	2400	2133	2133	1866	Mb/s
		1 rank DIMM(2)(3)	2133	2133	1866	1866	1600	Mb/s
		2 rank DIMM(2)(5)	1866	1866	1600	1600	1600	Mb/s
DDR3	All FFV packages and FBVB900	Single rank component	2133	2133	2133	2133	1866	Mb/s
		1 rank DIMM(2)(3)	1866	1866	1866	1866	1600	Mb/s
		2 rank DIMM(2)(5)	1600	1600	1600	1600	1333	Mb/s
		4 rank DIMM(2)(6)	1066	1066	1066	1066	800	Mb/s
	SFVC784	Single rank component	1866	1866	1866	1866	1600	Mb/s
		1 rank DIMM(2)(3)	1600	1600	1600	1600	1600	Mb/s
		2 rank DIMM(2)(5)	1600	1600	1600	1600	1333	Mb/s
		4 rank DIMM(2)(6)	1066	1066	1066	1066	800	Mb/s

Table 74: **Maximum Physical Interface (PHY) Rate for Memory Interfaces *(Cont'd)***

Memory Standard	Package(1)	DRAM Type	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
DDR3L	All FFV packages and FBVB900	Single rank component	1866	1866	1866	1866	1600	Mb/s
		1 rank DIMM(2)(3)	1600	1600	1600	1600	1333	Mb/s
		2 rank DIMM(2)(5)	1333	1333	1333	1333	1066	Mb/s
		4 rank DIMM(2)(6)	800	800	800	800	606	Mb/s
	SFVC784	Single rank component	1600	1600	1600	1600	1600	Mb/s
		1 rank DIMM(2)(3)	1600	1600	1600	1600	1333	Mb/s
		2 rank DIMM(2)(5)	1333	1333	1333	1333	1066	Mb/s
		4 rank DIMM(2)(6)	800	800	800	800	606	Mb/s
QDR II+	All	Single rank component(7)	633	633	600	600	550	MHz
RLDRAM 3	All FFV packages and FBVB900	Single rank component	1200	1200	1066	1066	933	MHz
	SFVC784	Single rank component	1066	1066	933	933	800	MHz
QDR IV XP	All	Single rank component	1066	1066	1066	933	933	MHz
LPDDR3	All	Single rank component	1600	1600	1600	1600	1600	Mb/s

Notes:

1. The SBVA484 and SFVA625 packages do not support the PL memory interfaces.
2. Dual in-line memory module (DIMM) includes RDIMM, SODIMM, UDIMM, and LRDIMM.
3. Includes: 1 rank 1 slot, DDP 2 rank, LRDIMM 2 or 4 rank 1 slot.
4. For the DDR4 DDP components at -3 and -2 speed grades and V_{CCINT} = 0.85V, the maximum data rate is 2133 Mb/s for six or more DDP devices. For five or less DDP devices, use the single rank DIMM data rates for the -3 and -2 speed grades at 0.85V.
5. Includes: 2 rank 1 slot, 1 rank 2 slot, LRDIMM 2 rank 2 slot.
6. Includes: 2 rank 2 slot, 4 rank 1 slot.
7. The QDRII+ performance specifications are for burst-length 4 (BL = 4) implementations.

Table 76: **IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
DIFF_SSTL12_F	0.394	0.394	0.402	0.394	0.402	0.412	0.412	0.430	0.412	0.430	0.538	0.538	0.566	0.538	0.566	ns
DIFF_SSTL12_M	0.394	0.394	0.402	0.394	0.402	0.553	0.553	0.584	0.553	0.584	0.641	0.641	0.676	0.641	0.676	ns
DIFF_SSTL12_S	0.394	0.394	0.402	0.394	0.402	0.758	0.758	0.808	0.758	0.808	0.823	0.823	0.879	0.823	0.879	ns
DIFF_SSTL135_DCI_F	0.371	0.371	0.402	0.371	0.402	0.411	0.411	0.428	0.411	0.428	0.537	0.537	0.565	0.537	0.565	ns
DIFF_SSTL135_DCI_M	0.371	0.371	0.402	0.371	0.402	0.551	0.551	0.582	0.551	0.582	0.645	0.645	0.685	0.645	0.685	ns
DIFF_SSTL135_DCI_S	0.371	0.371	0.402	0.371	0.402	0.746	0.746	0.799	0.746	0.799	0.829	0.829	0.893	0.829	0.893	ns
DIFF_SSTL135_F	0.375	0.375	0.402	0.375	0.402	0.408	0.408	0.428	0.408	0.428	0.528	0.528	0.561	0.528	0.561	ns
DIFF_SSTL135_M	0.375	0.375	0.402	0.375	0.402	0.555	0.555	0.585	0.555	0.585	0.641	0.641	0.679	0.641	0.679	ns
DIFF_SSTL135_S	0.375	0.375	0.402	0.375	0.402	0.772	0.772	0.823	0.772	0.823	0.827	0.827	0.878	0.827	0.878	ns
DIFF_SSTL15_DCI_F	0.397	0.397	0.417	0.397	0.417	0.412	0.412	0.429	0.412	0.429	0.531	0.531	0.563	0.531	0.563	ns
DIFF_SSTL15_DCI_M	0.397	0.397	0.417	0.397	0.417	0.553	0.553	0.583	0.553	0.583	0.645	0.645	0.685	0.645	0.685	ns
DIFF_SSTL15_DCI_S	0.397	0.397	0.417	0.397	0.417	0.768	0.768	0.822	0.768	0.822	0.847	0.847	0.912	0.847	0.912	ns
DIFF_SSTL15_F	0.404	0.404	0.417	0.404	0.417	0.424	0.424	0.445	0.424	0.445	0.551	0.551	0.577	0.551	0.577	ns
DIFF_SSTL15_M	0.404	0.404	0.417	0.404	0.417	0.554	0.554	0.585	0.554	0.585	0.639	0.639	0.677	0.639	0.677	ns
DIFF_SSTL15_S	0.404	0.404	0.417	0.404	0.417	0.767	0.767	0.817	0.767	0.817	0.813	0.813	0.867	0.813	0.867	ns
DIFF_SSTL18_I_DCI_F	0.320	0.320	0.336	0.320	0.336	0.445	0.445	0.461	0.445	0.461	0.566	0.566	0.595	0.566	0.595	ns
DIFF_SSTL18_I_DCI_M	0.320	0.320	0.336	0.320	0.336	0.554	0.554	0.585	0.554	0.585	0.644	0.644	0.683	0.644	0.683	ns
DIFF_SSTL18_I_DCI_S	0.320	0.320	0.336	0.320	0.336	0.762	0.762	0.818	0.762	0.818	0.837	0.837	0.899	0.837	0.899	ns
DIFF_SSTL18_I_F	0.316	0.316	0.336	0.316	0.336	0.454	0.454	0.476	0.454	0.476	0.578	0.578	0.608	0.578	0.608	ns
DIFF_SSTL18_I_M	0.316	0.316	0.336	0.316	0.336	0.571	0.571	0.603	0.571	0.603	0.652	0.652	0.692	0.652	0.692	ns
DIFF_SSTL18_I_S	0.316	0.316	0.336	0.316	0.336	0.782	0.782	0.835	0.782	0.835	0.816	0.816	0.870	0.816	0.870	ns
HSLVDCI_15_F	0.393	0.393	0.415	0.393	0.415	0.425	0.425	0.443	0.425	0.443	0.548	0.548	0.579	0.548	0.579	ns
HSLVDCI_15_M	0.393	0.393	0.415	0.393	0.415	0.552	0.552	0.581	0.552	0.581	0.644	0.644	0.684	0.644	0.684	ns
HSLVDCI_15_S	0.393	0.393	0.415	0.393	0.415	0.748	0.748	0.802	0.748	0.802	0.827	0.827	0.890	0.827	0.890	ns
HSLVDCI_18_F	0.424	0.424	0.447	0.424	0.447	0.445	0.445	0.461	0.445	0.461	0.566	0.566	0.595	0.566	0.595	ns
HSLVDCI_18_M	0.424	0.424	0.447	0.424	0.447	0.567	0.567	0.598	0.567	0.598	0.658	0.658	0.699	0.658	0.699	ns
HSLVDCI_18_S	0.424	0.424	0.447	0.424	0.447	0.761	0.761	0.817	0.761	0.817	0.836	0.836	0.900	0.836	0.900	ns
HSTL_I_12_F	0.378	0.378	0.399	0.378	0.399	0.423	0.423	0.443	0.423	0.443	0.553	0.553	0.582	0.553	0.582	ns
HSTL_I_12_M	0.378	0.378	0.399	0.378	0.399	0.551	0.551	0.582	0.551	0.582	0.642	0.642	0.679	0.642	0.679	ns
HSTL_I_12_S	0.378	0.378	0.399	0.378	0.399	0.750	0.750	0.799	0.750	0.799	0.813	0.813	0.868	0.813	0.868	ns
HSTL_I_18_F	0.322	0.322	0.339	0.322	0.339	0.456	0.456	0.474	0.456	0.474	0.576	0.576	0.606	0.576	0.606	ns
HSTL_I_18_M	0.322	0.322	0.339	0.322	0.339	0.569	0.569	0.602	0.569	0.602	0.653	0.653	0.692	0.653	0.692	ns
HSTL_I_18_S	0.322	0.322	0.339	0.322	0.339	0.781	0.781	0.833	0.781	0.833	0.816	0.816	0.871	0.816	0.871	ns
HSTL_I_DCI_12_F	0.378	0.378	0.399	0.378	0.399	0.406	0.406	0.429	0.406	0.429	0.534	0.534	0.564	0.534	0.564	ns
HSTL_I_DCI_12_M	0.378	0.378	0.399	0.378	0.399	0.556	0.556	0.586	0.556	0.586	0.654	0.654	0.694	0.654	0.694	ns
HSTL_I_DCI_12_S	0.378	0.378	0.399	0.378	0.399	0.754	0.754	0.803	0.754	0.803	0.842	0.842	0.907	0.842	0.907	ns
HSTL_I_DCI_18_F	0.321	0.321	0.339	0.321	0.339	0.445	0.445	0.461	0.445	0.461	0.566	0.566	0.595	0.566	0.595	ns
HSTL_I_DCI_18_M	0.321	0.321	0.339	0.321	0.339	0.554	0.554	0.585	0.554	0.585	0.643	0.643	0.684	0.643	0.684	ns
HSTL_I_DCI_18_S	0.321	0.321	0.339	0.321	0.339	0.761	0.761	0.817	0.761	0.817	0.836	0.836	0.900	0.836	0.900	ns
HSTL_I_DCI_F	0.393	0.393	0.415	0.393	0.415	0.431	0.431	0.445	0.431	0.445	0.555	0.555	0.575	0.555	0.575	ns
HSTL_I_DCI_M	0.393	0.393	0.415	0.393	0.415	0.552	0.552	0.581	0.552	0.581	0.644	0.644	0.684	0.644	0.684	ns

Table 76: **IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
SSTL135_DCI_S	0.366	0.366	0.399	0.366	0.399	0.746	0.746	0.799	0.746	0.799	0.829	0.829	0.893	0.829	0.893	ns
SSTL135_F	0.378	0.378	0.399	0.378	0.399	0.408	0.408	0.428	0.408	0.428	0.528	0.528	0.561	0.528	0.561	ns
SSTL135_M	0.378	0.378	0.399	0.378	0.399	0.555	0.555	0.585	0.555	0.585	0.641	0.641	0.679	0.641	0.679	ns
SSTL135_S	0.378	0.378	0.399	0.378	0.399	0.772	0.772	0.823	0.772	0.823	0.827	0.827	0.878	0.827	0.878	ns
SSTL15_DCI_F	0.402	0.402	0.417	0.402	0.417	0.412	0.412	0.429	0.412	0.429	0.531	0.531	0.563	0.531	0.563	ns
SSTL15_DCI_M	0.402	0.402	0.417	0.402	0.417	0.553	0.553	0.583	0.553	0.583	0.645	0.645	0.685	0.645	0.685	ns
SSTL15_DCI_S	0.402	0.402	0.417	0.402	0.417	0.768	0.768	0.822	0.768	0.822	0.847	0.847	0.912	0.847	0.912	ns
SSTL15_F	0.371	0.371	0.400	0.371	0.400	0.408	0.408	0.428	0.408	0.428	0.530	0.530	0.556	0.530	0.556	ns
SSTL15_M	0.371	0.371	0.400	0.371	0.400	0.554	0.554	0.585	0.554	0.585	0.639	0.639	0.677	0.639	0.677	ns
SSTL15_S	0.371	0.371	0.400	0.371	0.400	0.767	0.767	0.817	0.767	0.817	0.813	0.813	0.867	0.813	0.867	ns
SSTL18_I_DCI_F	0.329	0.329	0.336	0.329	0.336	0.445	0.445	0.461	0.445	0.461	0.566	0.566	0.595	0.566	0.595	ns
SSTL18_I_DCI_M	0.329	0.329	0.336	0.329	0.336	0.554	0.554	0.585	0.554	0.585	0.644	0.644	0.683	0.644	0.683	ns
SSTL18_I_DCI_S	0.329	0.329	0.336	0.329	0.336	0.762	0.762	0.818	0.762	0.818	0.837	0.837	0.899	0.837	0.899	ns
SSTL18_I_F	0.316	0.316	0.337	0.316	0.337	0.454	0.454	0.476	0.454	0.476	0.578	0.578	0.608	0.578	0.608	ns
SSTL18_I_M	0.316	0.316	0.337	0.316	0.337	0.571	0.571	0.603	0.571	0.603	0.652	0.652	0.692	0.652	0.692	ns
SSTL18_I_S	0.316	0.316	0.337	0.316	0.337	0.782	0.782	0.835	0.782	0.835	0.816	0.816	0.870	0.816	0.870	ns
SUB_LVDS	0.539	0.539	0.620	0.539	0.620	0.660	0.660	0.692	0.660	0.692	969.863	969.863	969.863	969.863	969.863	ns

IOB 3-state Output Switching Characteristics

Table 77 specifies the values of $T_{OUTBUF\_DELAY\_TE\_PAD}$ and $T_{INBUF\_DELAY\_IBUFDIS\_O}$. $T_{OUTBUF\_DELAY\_TE\_PAD}$ is the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{INBUF\_DELAY\_IBUFDIS\_O}$ is the IOB delay from IBUFDISABLE to O output. In HP I/O banks, the internal DCI termination turn-off time is always faster than $T_{OUTBUF\_DELAY\_TE\_PAD}$ when the DCITERMDISABLE pin is used. In HD I/O banks, the internal IN_TERM termination turn-off time is always faster than $T_{OUTBUF\_DELAY\_TE\_PAD}$ when the INTERMDISABLE pin is used.

Table 77: **IOB 3-state Output Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
$T_{OUTBUF\_DELAY\_TE\_PAD}$	T input to pad high-impedance for HD I/O banks	6.318	6.318	6.369	6.318	6.369	ns
	T input to pad high-impedance for HP I/O banks	5.330	5.330	5.341	5.330	5.341	ns
$T_{INBUF\_DELAY\_IBUFDIS\_O}$	IBUF turn-on time from IBUFDISABLE to O output for HD I/O banks	2.266	2.266	2.430	2.266	2.430	ns
	IBUF turn-on time from IBUFDISABLE to O output for HP I/O banks	0.936	0.936	1.037	0.936	1.037	ns

Table 78: **Input Delay Measurement Methodology *(Cont'd)***

Description	I/O Standard Attribute	V_L (1)(2)	V_H (1)(2)	V_{MEAS} (1)(4)(6)	V_{REF} (1)(3)(5)
SUB_LVDS, 1.8V	SUB_LVDS	0.9 – 0.125	0.9 + 0.125	0(6)	–
SLVS, 1.8V	SLVS_400_18	0.9 – 0.125	0.9 + 0.125	0(6)	–
SLVS, 2.5V	SLVS_400_25	1.25 – 0.125	1.25 + 0.125	0(6)	–
LVPECL, 2.5V	LVPECL	1.25 – 0.125	1.25 + 0.125	0(6)	–
MIPI D-PHY (high speed) 1.2V	MIPI_DPHY_DCI_HS	0.2 – 0.125	0.2 + 0.125	0(6)	–
MIPI D-PHY (low power) 1.2V	MIPI_DPHY_DCI_LP	0.715 – 0.2	0.715 + 0.2	0(6)	–

Notes:

1. The input delay measurement methodology parameters for LVDCI/HSLVDCI are the same for LVCMOS standards of the same voltage. Parameters for all other DCI standards are the same for the corresponding non-DCI standards.
2. Input waveform switches between V_L and V_H.
3. Measurements are made at typical, minimum, and maximum V_{REF} values. Reported delays reflect worst case of these measurements. V_{REF} values listed are typical.
4. Input voltage level from which measurement starts.
5. This is an input voltage reference that bears no relation to the V_{REF}/V_{MEAS} parameters found in IBIS models and/or noted in Figure 1.
6. The value given is the differential input voltage.

Output Delay Measurement Methodology

Output delays are measured with short output traces. Standard termination was used for all testing. The propagation delay of the trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in Figure 1 and Figure 2.

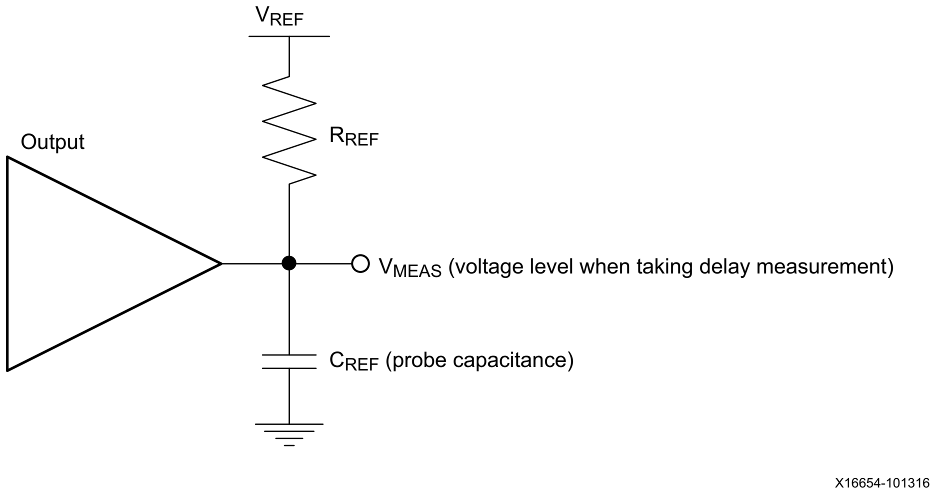

Figure 1: **Single-Ended Test Setup**

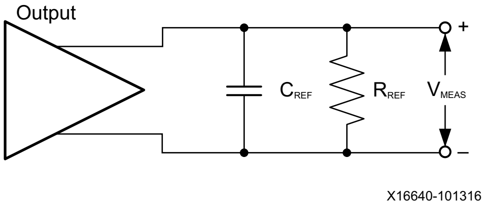

Figure 2: **Differential Test Setup**

Parameters V_{REF}, R_{REF}, C_{REF}, and V_{MEAS} fully describe the test conditions for each I/O standard. The most accurate prediction of propagation delay in any given application can be obtained through IBIS simulation, using this method:

1. Simulate the output driver of choice into the generalized test setup using values from Table 79.
2. Record the time to V_{MEAS}.
3. Simulate the output driver of choice into the actual PCB trace and load using the appropriate IBIS model or capacitance value to represent the load.
4. Record the time to V_{MEAS}.
5. Compare the results of step 2 and step 4. The increase or decrease in delay yields the actual propagation delay of the PCB trace.

Table 79: **Output Delay Measurement Methodology**

Description	I/O Standard Attribute	R_{REF} (Ω)	C_{REF}(1) (pF)	V_{MEAS} (V)	V_{REF} (V)
LVCMOS, 1.2V	LVCMOS12	1M	0	0.6	0
LVCMOS, 1.5V	LVCMOS15	1M	0	0.75	0
LVCMOS, 1.8V	LVCMOS18	1M	0	0.9	0
LVCMOS, 2.5V	LVCMOS25	1M	0	1.25	0
LVCMOS, 3.3V	LVCMOS33	1M	0	1.65	0
LVTTL, 3.3V	LVTTL	1M	0	1.65	0
LVDCI, HSLVDCI, 1.5V	LVDCI_15, HSLVDCI_15	50	0	V_{REF}	0.75
LVDCI, HSLVDCI, 1.8V	LVDCI_15, HSLVDCI_18	50	0	V_{REF}	0.9
HSTL (high-speed transceiver logic), class I, 1.2V	HSTL_I_12	50	0	V_{REF}	0.6
HSTL, class I, 1.5V	HSTL_I	50	0	V_{REF}	0.75
HSTL, class I, 1.8V	HSTL_I_18	50	0	V_{REF}	0.9
HSUL (high-speed unterminated logic), 1.2V	HSUL_12	50	0	V_{REF}	0.6
SSTL12 (stub series terminated logic), 1.2V	SSTL12	50	0	V_{REF}	0.6
SSTL135 and SSTL135 class II, 1.35V	SSTL135, SSTL135_II	50	0	V_{REF}	0.675
SSTL15 and SSTL15 class II, 1.5V	SSTL15, SSTL15_II	50	0	V_{REF}	0.75
SSTL18, class I and class II, 1.8V	SSTL18_I, SSTL18_II	50	0	V_{REF}	0.9
POD10, 1.0V	POD10	50	0	V_{REF}	1.0
POD12, 1.2V	POD12	50	0	V_{REF}	1.2
DIFF_HSTL, class I, 1.2V	DIFF_HSTL_I_12	50	0	V_{REF}	0.6
DIFF_HSTL, class I, 1.5V	DIFF_HSTL_I	50	0	V_{REF}	0.75
DIFF_HSTL, class I, 1.8V	DIFF_HSTL_I_18	50	0	V_{REF}	0.9
DIFF_HSUL, 1.2V	DIFF_HSUL_12	50	0	V_{REF}	0.6
DIFF_SSTL12, 1.2V	DIFF_SSTL12	50	0	V_{REF}	0.6
DIFF_SSTL135 and DIFF_SSTL135 class II, 1.35V	DIFF_SSTL135, DIFF_SSTL135_II	50	0	V_{REF}	0.675
DIFF_SSTL15 and DIFF_SSTL15 class II, 1.5V	DIFF_SSTL15, DIFF_SSTL15_II	50	0	V_{REF}	0.75
DIFF_SSTL18, class I and II, 1.8V	DIFF_SSTL18_I, DIFF_SSTL18_II	50	0	V_{REF}	0.9
DIFF_POD10, 1.0V	DIFF_POD10	50	0	V_{REF}	1.0
DIFF_POD12, 1.2V	DIFF_POD12	50	0	V_{REF}	1.2
LVDS (low-voltage differential signaling), 1.8V	LVDS	100	0	0(2)	0
SUB_LVDS, 1.8V	SUB_LVDS	100	0	0(2)	0
MIPI D-PHY (high speed) 1.2V	MIPI_DPHY_DCI_HS	100	0	0(2)	0
MIPI D-PHY (low power) 1.2V	MIPI_DPHY_DCI_LP	1M	0	0.6	0

Notes:

1. C_{REF} is the capacitance of the probe, nominally 0 pF.
2. The value given is the differential output voltage.

Block RAM and FIFO Switching Characteristics

Table 80: **Block RAM and FIFO Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
Maximum Frequency							
$F_{MAX\_WF\_NC}$	Block RAM (WRITE_FIRST and NO_CHANGE modes).	825	738	645	585	516	MHz
F_{MAX_RF}	Block RAM (READ_FIRST mode).	718	637	575	510	460	MHz
F_{MAX_FIFO}	FIFO in all modes without ECC.	825	738	645	585	516	MHz
F_{MAX_ECC}	Block RAM and FIFO in ECC configuration without PIPELINE.	718	637	575	510	460	MHz
	Block RAM and FIFO in ECC configuration with PIPELINE and Block RAM in WRITE_FIRST or NO_CHANGE mode.	825	738	645	585	516	MHz
T_{PW}(1)	Minimum pulse width.	495	542	543	577	578	ps
Block RAM and FIFO Clock-to-Out Delays							
T_{RCKO_DO}	Clock CLK to DOUT output (without output register).	0.91	1.02	1.11	1.46	1.53	ns, Max
$T_{RCKO\_DO\_REG}$	Clock CLK to DOUT output (with output register).	0.27	0.29	0.30	0.42	0.44	ns, Max

Notes:

1. The MMCM and PLL DUTY_CYCLE attribute should be set to 50% to meet the pulse-width requirements at the higher frequencies.

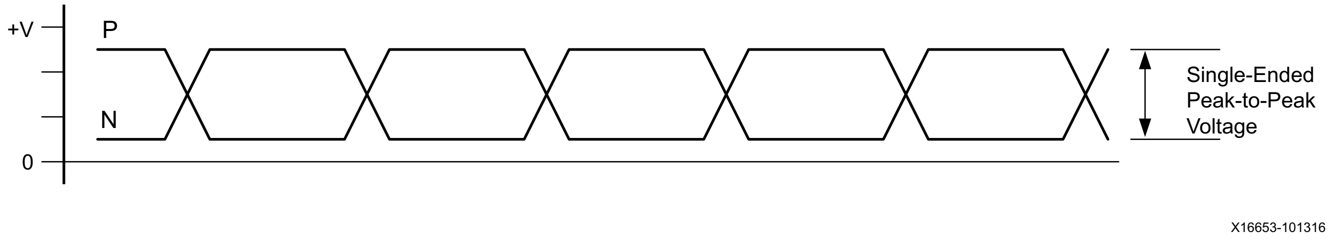

Figure 3: **Single-Ended Peak-to-Peak Voltage**

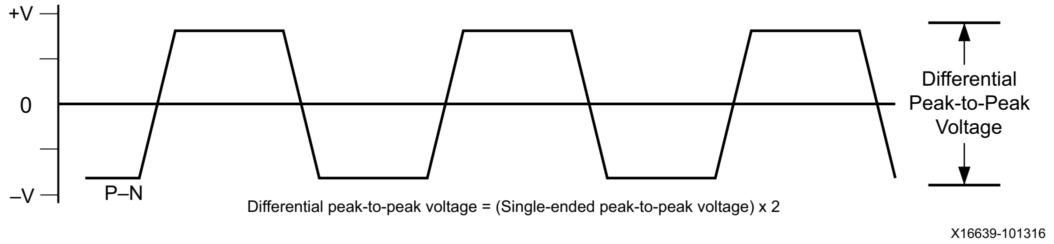

Figure 4: **Differential Peak-to-Peak Voltage**

Table 95 and Table 96 summarize the DC specifications of the GTH transceivers input and output clocks in Zynq UltraScale+ MPSoC. Consult the *UltraScale Architecture GTH Transceiver User Guide* (UG576) for further details.

Table 95: **GTH Transceiver Clock Input Level Specification**

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage.	250	–	2000	mV
R_{IN}	Differential input resistance.	–	100	–	Ω
C_{EXT}	Required external AC coupling capacitor.	–	10	–	nF

Table 96: **GTH Transceiver Clock Output Level Specification**

Symbol	Description	Conditions	Min	Typ	Max	Units
V_{OL}	Output Low voltage for P and N.	R_T = 100Ω across P and N signals	100	–	330	mV
V_{OH}	Output High voltage for P and N.	R_T = 100Ω across P and N signals	500	–	700	mV
V_{DDOUT}	Differential output voltage. (P–N), P = High (N–P), N = High	R_T = 100Ω across P and N signals	300	–	430	mV
V_{CMOUT}	Common mode voltage.	R_T = 100Ω across P and N signals	300	–	500	mV

Table 99: **GTH Transceiver Reference Clock Switching Characteristics**

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F_{GCLK}	Reference clock frequency range.		60	–	820	MHz
T_{RCLK}	Reference clock rise time.	20% – 80%	–	200	–	ps
T_{FCLK}	Reference clock fall time.	80% – 20%	–	200	–	ps
T_{DCREF}	Reference clock duty cycle.	Transceiver PLL only	40	50	60	%

Table 100: **GTH Transceiver Reference Clock Oscillator Selection Phase Noise Mask**

Symbol	Description	Offset Frequency	Min	Typ	Max	Units
$QPLL_{REFCLKMASK}$(1)(2)	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	–	–	–105	dBc/Hz
		100 kHz	–	–	–124	
		1 MHz	–	–	–130	
$CPLL_{REFCLKMASK}$(1)(2)	CPLL reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	–	–	–105	dBc/Hz
		100 kHz	–	–	–124	
		1 MHz	–	–	–130	
		50 MHz	–	–	–140	

Notes:

1. For reference clock frequencies other than 312.5 MHz, adjust the phase-noise mask values by 20 x Log(N/312.5) where N is the new reference clock frequency in MHz.
2. This reference clock phase-noise mask is superseded by any reference clock phase-noise mask that is specified in a supported protocol, e.g., PCIe.

Table 101: **GTH Transceiver PLL/Lock Time Adaptation**

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
T_{LOCK}	Initial PLL lock.		–	–	1	ms
T_{DLOCK}	Clock recovery phase acquisition and adaptation time for decision feedback equalizer (DFE).	After the PLL is locked to the reference clock, this is the time it takes to lock the clock data recovery (CDR) to the data present at the input.	–	50,000	37×10^6	UI
	Clock recovery phase acquisition and adaptation time for low-power mode (LPM) when the DFE is disabled.		–	50,000	2.3×10^6	UI

Table 102: **GTH Transceiver User Clock Switching Characteristics**(1)

Symbol	Description	Data Width Conditions (Bit)		Speed Grade and V_{CCINT} Operating Voltages					Units
				0.90V	0.85V		0.72V		
		Internal Logic	Interconnect Logic	-3(2)	-2(2)(3)	-1(4)(5)	-2(3)	-1(5)	
$F_{TXOUTPMA}$	TXOUTCLK maximum frequency sourced from OUTCLKPMA			511.719	511.719	390.625	390.625	322.266	MHz
$F_{RXOUTPMA}$	RXOUTCLK maximum frequency sourced from OUTCLKPMA			511.719	511.719	390.625	390.625	322.266	MHz

Table 102: **GTH Transceiver User Clock Switching Characteristics[1] *(Cont'd)***

Symbol	Description	Data Width Conditions (Bit)		Speed Grade and V_{CCINT} Operating Voltages					Units
				0.90V	0.85V		0.72V		
		Internal Logic	Interconnect Logic	-3[2]	-2[2][3]	-1[4][5]	-2[3]	-1[5]	
$F_{TXOUTPROGDIV}$	TXOUTCLK maximum frequency sourced from TXPROGDIVCLK			511.719	511.719	511.719	511.719	511.719	MHz
$F_{RXOUTPROGDIV}$	RXOUTCLK maximum frequency sourced from RXPROGDIVCLK			511.719	511.719	511.719	511.719	511.719	MHz
F_{TXIN}	TXUSRCLK[6] maximum frequency	16	16, 32	511.719	511.719	390.625	390.625	322.266	MHz
		32	32, 64	511.719	511.719	390.625	390.625	322.266	MHz
		20	20, 40	409.375	409.375	312.500	312.500	257.813	MHz
		40	40, 80	409.375	409.375	312.500	312.500	257.813	MHz
F_{RXIN}	RXUSRCLK[6] maximum frequency	16	16, 32	511.719	511.719	390.625	390.625	322.266	MHz
		32	32, 64	511.719	511.719	390.625	390.625	322.266	MHz
		20	20, 40	409.375	409.375	312.500	312.500	257.813	MHz
		40	40, 80	409.375	409.375	312.500	312.500	257.813	MHz
F_{TXIN2}	TXUSRCLK2[6] maximum frequency	16	16	511.719	511.719	390.625	390.625	322.266	MHz
		16	32	255.859	255.859	195.313	195.313	161.133	MHz
		32	32	511.719	511.719	390.625	390.625	322.266	MHz
		32	64	255.859	255.859	195.313	195.313	161.133	MHz
		20	20	409.375	409.375	312.500	312.500	257.813	MHz
		20	40	204.688	204.688	156.250	156.250	128.906	MHz
		40	40	409.375	409.375	312.500	312.500	257.813	MHz
		40	80	204.688	204.688	156.250	156.250	128.906	MHz
F_{RXIN2}	RXUSRCLK2[6] maximum frequency	16	16	511.719	511.719	390.625	390.625	322.266	MHz
		16	32	255.859	255.859	195.313	195.313	161.133	MHz
		32	32	511.719	511.719	390.625	390.625	322.266	MHz
		32	64	255.859	255.859	195.313	195.313	161.133	MHz
		20	20	409.375	409.375	312.500	312.500	257.813	MHz
		20	40	204.688	204.688	156.250	156.250	128.906	MHz
		40	40	409.375	409.375	312.500	312.500	257.813	MHz
		40	80	204.688	204.688	156.250	156.250	128.906	MHz

Notes:

1. Clocking must be implemented as described in *UltraScale Architecture GTH Transceiver User Guide* (UG576).
2. For speed grades -3E, -2E, and -2I, a 16-bit and 20-bit internal data path can only be used for line rates less than 8.1875 Gb/s.
3. For speed grade -2LE, a 16-bit and 20-bit internal data path can only be used for line rates less than 8.1875 Gb/s when V_{CCINT} = 0.85V or 6.25 Gb/s when V_{CCINT} = 0.72V.
4. For speed grades -1E and -1I, a 16-bit and 20-bit internal data path can only be used for line rates less than 6.25 Gb/s.
5. For speed grade -1LI, a 16-bit and 20-bit internal data path can only be used for line rates less than 6.25 Gb/s when V_{CCINT} = 0.85V or 5.15625 Gb/s when V_{CCINT} = 0.72V.
6. When the gearbox is used, these maximums refer to the XCLK. For more information, see the *Valid Data Width Combinations for TX Asynchronous Gearbox* table in the *UltraScale Architecture GTH Transceiver User Guide* (UG576).

Table 103: **GTH Transceiver Transmitter Switching Characteristics *(Cont'd)***

Symbol	Description	Condition	Min	Typ	Max	Units
$T_{J2.5}$	Total jitter(3)(4)	2.5 Gb/s(6)	–	–	0.20	UI
$D_{J2.5}$	Deterministic jitter(3)(4)		–	–	0.10	UI
$T_{J1.25}$	Total jitter(3)(4)	1.25 Gb/s(7)	–	–	0.15	UI
$D_{J1.25}$	Deterministic jitter(3)(4)		–	–	0.06	UI
T_{J500}	Total jitter(3)(4)	500 Mb/s(8)	–	–	0.10	UI
D_{J500}	Deterministic jitter(3)(4)		–	–	0.03	UI

Notes:

1. Using same REFCLK input with TX phase alignment enabled for up to four consecutive transmitters (one fully populated GTH Quad) at the maximum line rate.
2. Using QPLL_FBDIV = 40, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
3. Using CPLL_FBDIV = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
4. All jitter values are based on a bit-error ratio of 10^{-12}.
5. CPLL frequency at 3.2 GHz and TXOUT_DIV = 2.
6. CPLL frequency at 2.5 GHz and TXOUT_DIV = 2.
7. CPLL frequency at 2.5 GHz and TXOUT_DIV = 4.
8. CPLL frequency at 2.0 GHz and TXOUT_DIV = 8.

Table 104: **GTH Transceiver Receiver Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTHRX}	Serial data rate		0.500	–	F_{GTHMAX}	Gb/s
R_{XSST}	Receiver spread-spectrum tracking(1)	Modulated at 33 kHz	–5000	–	0	ppm
R_{XRL}	Run length (CID)		–	–	256	UI
$R_{XPPMTOL}$	Data/REFCLK PPM offset tolerance	Bit rates ≤ 6.6 Gb/s	–1250	–	1250	ppm
		Bit rates > 6.6 Gb/s and ≤ 8.0 Gb/s	–700	–	700	ppm
		Bit rates > 8.0 Gb/s	–200	–	200	ppm
SJ Jitter Tolerance(2)						
$J_{T\_SJ16.375}$	Sinusoidal jitter (QPLL)(3)	16.375 Gb/s	0.30	–	–	UI
$J_{T\_SJ15.0}$	Sinusoidal jitter (QPLL)(3)	15.0 Gb/s	0.30	–	–	UI
$J_{T\_SJ14.1}$	Sinusoidal jitter (QPLL)(3)	14.1 Gb/s	0.30	–	–	UI
$J_{T\_SJ13.1}$	Sinusoidal jitter (QPLL)(3)	13.1 Gb/s	0.30	–	–	UI
$J_{T\_SJ12.5}$	Sinusoidal jitter (QPLL)(3)	12.5 Gb/s	0.30	–	–	UI
$J_{T\_SJ11.3}$	Sinusoidal jitter (QPLL)(3)	11.3 Gb/s	0.30	–	–	UI
$J_{T\_SJ10.32\_QPLL}$	Sinusoidal jitter (QPLL)(3)	10.32 Gb/s	0.30	–	–	UI
$J_{T\_SJ10.32\_CPLL}$	Sinusoidal jitter (CPLL)(3)	10.32 Gb/s	0.30	–	–	UI
$J_{T\_SJ9.953\_QPLL}$	Sinusoidal jitter (QPLL)(3)	9.953 Gb/s	0.30	–	–	UI
$J_{T\_SJ9.953\_CPLL}$	Sinusoidal jitter (CPLL)(3)	9.953 Gb/s	0.30	–	–	UI
$J_{T\_SJ8.0}$	Sinusoidal jitter (QPLL)(3)	8.0 Gb/s	0.42	–	–	UI
$J_{T\_SJ6.6\_CPLL}$	Sinusoidal jitter (CPLL)(3)	6.6 Gb/s	0.44	–	–	UI
$J_{T\_SJ5.0}$	Sinusoidal jitter (CPLL)(3)	5.0 Gb/s	0.44	–	–	UI
$J_{T\_SJ4.25}$	Sinusoidal jitter (CPLL)(3)	4.25 Gb/s	0.44	–	–	UI
$J_{T\_SJ3.2}$	Sinusoidal jitter (CPLL)(3)	3.2 Gb/s(4)	0.45	–	–	UI

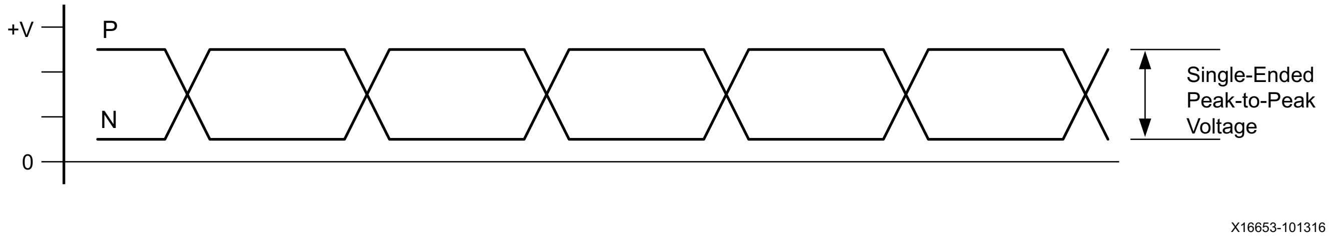

Figure 5: **Single-Ended Peak-to-Peak Voltage**

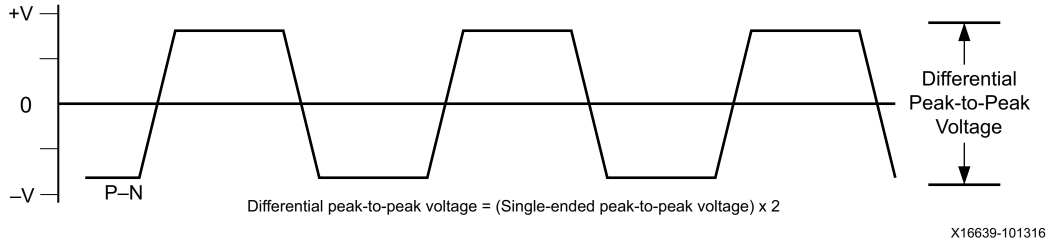

Figure 6: **Differential Peak-to-Peak Voltage**

Table 107 and Table 108 summarize the DC specifications of the clock input of the GTY transceivers in Zynq UltraScale+ MPSoCs. Consult the *UltraScale Architecture GTY Transceiver User Guide* (UG578) for further details.

Table 107: **GTY Transceiver Clock DC Input Level Specification**

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage	250	–	2000	mV
R_{IN}	Differential input resistance	–	100	–	Ω
C_{EXT}	Required external AC coupling capacitor	–	10	–	nF

Table 108: **GTY Transceiver Clock Output Level Specification**

Symbol	Description	Conditions	Min	Typ	Max	Units
V_{OL}	Output Low voltage for P and N	R_T = 100Ω across P and N signals	100	–	330	mV
V_{OH}	Output High voltage for P and N	R_T = 100Ω across P and N signals	500	–	700	mV
V_{DDOUT}	Differential output voltage (P–N), P = High (N–P), N = High	R_T = 100Ω across P and N signals	300	–	430	mV
V_{CMOUT}	Common mode voltage	R_T = 100Ω across P and N signals	300	–	500	mV

Table 110: GTY Transceiver Dynamic Reconfiguration Port (DRP) Switching Characteristics

Symbol	Description	All Speed Grades	Units
$F_{GTYDRPCLK}$	GTYDRPCLK maximum frequency.	250	MHz

Table 111: GTY Transceiver Reference Clock Switching Characteristics

Symbol	Description	Conditions	All Speed Grades Min	Typ	Max	Units
F_{GCLK}	Reference clock frequency range.		60	–	820	MHz
T_{RCLK}	Reference clock rise time.	20% – 80%	–	200	–	ps
T_{FCLK}	Reference clock fall time.	80% – 20%	–	200	–	ps
T_{DCREF}	Reference clock duty cycle.	Transceiver PLL only	40	50	60	%

Table 112: GTY Transceiver Reference Clock Oscillator Selection Phase Noise Mask[1]

Symbol	Description	Offset Frequency	Min	Typ	Max	Units
$QPLL_{REFCLKMASK}$	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency = 156.25 MHz.	10 kHz	–	–	–112	dBc/Hz
		100 kHz	–	–	–128	
		1 MHz	–	–	–145	
	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	–	–	–103	dBc/Hz
		100 kHz	–	–	–123	
		1 MHz	–	–	–143	
	QPLL0/QPLL1 reference clock select phase noise mask at REFCLK frequency =625 MHz.	10 kHz	–	–	–98	dBc/Hz
		100 kHz	–	–	–117	
		1 MHz	–	–	–140	
$CPLL_{REFCLKMASK}$	CPLL reference clock select phase noise mask at REFCLK frequency = 156.25 MHz.	10 kHz	–	–	–112	dBc/Hz
		100 kHz	–	–	–128	
		1 MHz	–	–	–145	
		50 MHz	–	–	–145	
	CPLL reference clock select phase noise mask at REFCLK frequency = 312.5 MHz.	10 kHz	–	–	–103	dBc/Hz
		100 kHz	–	–	–123	
		1 MHz	–	–	–143	
		50 MHz	–	–	–145	
	CPLL reference clock select phase noise mask at REFCLK frequency = 625 MHz.	10 kHz	–	–	–98	dBc/Hz
		100 kHz	–	–	–117	
		1 MHz	–	–	–140	
		50 MHz	–	–	–144	

Notes:

1. For reference clock frequencies not in this table, use the phase-noise mask for the nearest reference clock frequency.
2. This reference clock phase-noise mask is superseded by any reference clock phase-noise mask that is specified in a supported protocol, e.g., PCIe.

Table 115: GTY Transceiver Transmitter Switching Characteristics

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTYTX}	Serial data rate range		0.500	–	F_{GTYMAX}	Gb/s
T_{RTX}	TX rise time	20%–80%	–	21	–	ps
T_{FTX}	TX fall time	80%–20%	–	21	–	ps
T_{LLSKEW}	TX lane-to-lane skew(1)		–	–	500.00	ps
$T_{J32.75}$	Total jitter(2)(4)	32.75 Gb/s	–	–	0.35	UI
$D_{J32.75}$	Deterministic jitter(2)(4)		–	–	0.19	UI
$T_{J28.21}$	Total jitter(2)(4)	28.21 Gb/s	–	–	0.28	UI
$D_{J28.21}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J16.375}$	Total jitter(2)(4)	16.375 Gb/s	–	–	0.28	UI
$D_{J16.375}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J15.0}$	Total jitter(2)(4)	15.0 Gb/s	–	–	0.28	UI
$D_{J15.0}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J14.1}$	Total jitter(2)(4)	14.1 Gb/s	–	–	0.28	UI
$D_{J14.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J14.1}$	Total jitter(2)(4)	14.025 Gb/s	–	–	0.28	UI
$D_{J14.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J13.1}$	Total jitter(2)(4)	13.1 Gb/s	–	–	0.28	UI
$D_{J13.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J12.5\_QPLL}$	Total jitter(2)(4)	12.5 Gb/s	–	–	0.28	UI
$D_{J12.5\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J12.5\_CPLL}$	Total jitter(3)(4)	12.5 Gb/s	–	–	0.33	UI
$D_{J12.5\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J11.3\_QPLL}$	Total jitter(2)(4)	11.3 Gb/s	–	–	0.28	UI
$D_{J11.3\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J10.3125\_QPLL}$	Total jitter(2)(4)	10.3125 Gb/s	–	–	0.28	UI
$D_{J10.3125\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J10.3125\_CPLL}$	Total jitter(3)(4)	10.3125 Gb/s	–	–	0.33	UI
$D_{J10.3125\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J9.953\_QPLL}$	Total jitter(2)(4)	9.953 Gb/s	–	–	0.28	UI
$D_{J9.953\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J9.953\_CPLL}$	Total jitter(3)(4)	9.953 Gb/s	–	–	0.33	UI
$D_{J9.953\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J8.0}$	Total jitter(3)(4)	8.0 Gb/s	–	–	0.32	UI
$D_{J8.0}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J6.6}$	Total jitter(3)(4)	6.6 Gb/s	–	–	0.30	UI
$D_{J6.6}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J5.0}$	Total jitter(3)(4)	5.0 Gb/s	–	–	0.30	UI
$D_{J5.0}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J4.25}$	Total jitter(3)(4)	4.25 Gb/s	–	–	0.30	UI
$D_{J4.25}$	Deterministic jitter(3)(4)		–	–	0.15	UI

Table 117: **GTY Transceiver Protocol List** ***(Cont'd)***

Protocol	Specification	Serial Rate (Gb/s)	Electrical Compliance
Serial RapidIO	RapidIO specification 3.1	1.25–10.3125	Compliant
DisplayPort	DP 1.2B CTS	1.62–5.4	Compliant(3)
Fibre channel	FC-PI-4	1.0625–14.025	Compliant
SATA Gen1, 2, 3	Serial ATA revision 3.0 specification	1.5, 3.0, and 6.0	Compliant
SAS Gen1, 2, 3	T10/BSR INCITS 519	3.0, 6.0, and 12.0	Compliant
SFI-5	OIF-SFI5-01.0	0.625 - 12.5	Compliant
Aurora	CEI-6G, CEI-11G-LR	All rates	Compliant

Notes:

1. 25 dB loss at Nyquist without FEC.
2. The transition time of the transmitter is faster than the IEEE Std 802.3-2012 specification.
3. This protocol requires external circuitry to achieve compliance.

Configuration Switching Characteristics

Table 127: **Configuration Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
PL Power-up Timing Characteristics							
T_{PL}	PS_PROG_B PL latency.	7.5	7.5	7.5	7.5	7.5	ms, Max
T_{POR}	Power-on reset from PL power-on to PL ready to configure (40 ms maximum ramp rate).	65	65	65	65	65	ms, Max
		0	0	0	0	0	ms, Min
	Power-on reset from PL power-on to PL ready to configure with POR override (2 ms maximum ramp rate).	15	15	15	15	15	ms, Max
		5	5	5	5	5	ms, Min
$T_{PS\_PROG\_B}$	PL program pulse width.	250	250	250	250	250	ns, Min
Internal Configuration Access Port							
F_{ICAPCK}	Internal configuration access port (ICAPE3).	200	200	200	150	150	MHz, Max
DNA Port Switching							
F_{DNACK}	DNA port frequency (DNA_PORT).	200	200	200	175	175	MHz, Max
STARTUPE3 Ports							
$F_{CFGMCLK}$	STARTUPE3 CFGMCLK output frequency.	50.00	50.00	50.00	50.00	50.00	MHz, Typ
$F_{CFGMCLKTOL}$	STARTUPE3 CFGMCLK output frequency tolerance.	±15	±15	±15	±15	±15	%, Max
T_{DCI_MATCH}	Specifies a stall in the startup cycle until the digitally controlled impedance (DCI) match signals are asserted.	4	4	4	4	4	ms, Max